

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S77	2270	(438/199,211,230,231).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/22 13:25
S3	8	(metal adj gate) and (hafnium adj nitride) and Hfn	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/22 13:25
S79	19	S77 and S78	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 13:26
S78	474	(electrode gate) with (hafnium near3 nitride HfN)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 13:32
S82	88	S81 and (CMOS)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 13:59
S83	2	("20010013600").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/22 14:18
S84	1	S82 and S83	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 14:31

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S85	3	hafnium near3 nitride with (((nitrogen "N.sub.2") and ("Ar" argon)) same chamber)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 14:32
S88	311	(hafnium near3 oxide "HfO.sub.2") same (MOCVD)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 15:01
S86	49	(hafnium "Hf") with (((nitrogen "N. sub.2") and ("Ar" argon)) same chamber)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 15:01
S87	32	S86 and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 15:02
S89	212	S88 and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 16:09
S91	39	("HfO.sub.2" or hafnium near3 oxide) same (post near3 anneal\$3) same (nitrogen Nitride "N.sub.2") and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 16:12
S90	3	(HfN or hafnium near3 nitride) same (post near3 anneal\$3) same (nitrogen Nitride "N.sub.2") and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 16:31

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S93	0	(gate near3 electrod same (HfN or hafnium near3 nitride)) and (("HfO. sub.2" hafnium near3 oxide) same dielectric) and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 16:32
S92	0	(gate near3 electrod same (HfN or hafnium near3 nitride)) and (("HfO. sub.2" hafnium near3 oxide) same dielectric)and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 16:32
S95	118	(gate near3 electrode same (HfN or hafnium near3 nitride)) and (("HfO. sub.2" hafnium near3 oxide) same dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 16:33
S94	0	(gate near3 electrod same (HfN or hafnium near3 nitride)) and (("HfO. sub.2" hafnium near3 oxide) same dielectric)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 16:33
S81	284	S78 and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 16:33
S97	2	("20050205947").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/22 17:22
S98	399	(dop\$3 impurity) same (HfN hafnium near3 nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 17:23

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S99	25930161	22and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 17:26
S96	53	S95 and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 17:26
S10 2	0	((Hafnum near3 nitride) same (work near3 function))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 17:36
S10 1	0	((Hafnum near3 nitride) same (work near3 function)) and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 17:36
S10 0	233	S98 and ((@ad<"20040317") or (@rlad<"20040317"))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 17:36
S10 3	0	((Hafnum near3 nitride) same (implant\$3 impurity dop\$3 (work near3 function)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 17:41
S10 4	235	((Hafnum near3 nitride HfN) same (implant\$3 impurity dop\$3 (work near3 function)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 17:50

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S11 1	2	("20040129995").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/22 17:55
S10 5	12	((Hafnum near3 nitride HfN) same ("RTA" thermal near3 anneal\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 17:58
S11 3	0	((Hafnum near3 nitride HfN) same (gate electrode) with ("RTA" thermal near3 anneal\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 18:00
S11 2	1	((Hafnum near3 nitride HfN) near10 (gate electrode) same ("RTA" thermal near3 anneal\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 18:00
S11 4	3	((Hafnum near3 nitride HfN) same (gate electrode) with ("RTA" thermal near3 anneal\$3 heat\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/22 18:01
S11 6	0	S115 and (HfN) near20 (CVD)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/23 10:46
S11 5	2	("20010013600").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/23 10:46

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S11 7	2	("20040157473").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/23 10:51
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